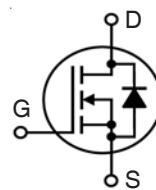
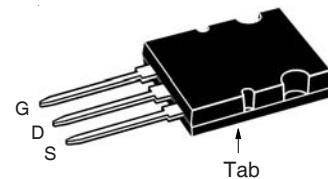


**X-Class HiPerFET™  
Power MOSFET**
**IXFB90N85X**

N-Channel Enhancement Mode  
Avalanche Rated  
Fast Intrinsic Diode

**V<sub>DSS</sub>** = 850V  
**I<sub>D25</sub>** = 90A  
**R<sub>DS(on)</sub>** ≤ 41mΩ


**PLUS264™**


G = Gate      D = Drain  
S = Source      Tab = Drain

Symbol	Test Conditions	Maximum Ratings		
V <sub>DSS</sub>	T <sub>J</sub> = 25°C to 150°C	850	V	
V <sub>DGR</sub>	T <sub>J</sub> = 25°C to 150°C, R <sub>GS</sub> = 1MΩ	850	V	
V <sub>GSS</sub>	Continuous	± 30	V	
V <sub>GSM</sub>	Transient	± 40	V	
I <sub>D25</sub>	T <sub>C</sub> = 25°C	90	A	
I <sub>DM</sub>	T <sub>C</sub> = 25°C, Pulse Width Limited by T <sub>JM</sub>	180	A	
I <sub>A</sub>	T <sub>C</sub> = 25°C	45	A	
E <sub>AS</sub>	T <sub>C</sub> = 25°C	4	J	
P <sub>D</sub>	T <sub>C</sub> = 25°C	1785	W	
dv/dt	I <sub>S</sub> ≤ I <sub>DM</sub> , V <sub>DD</sub> ≤ V <sub>DSS</sub> , T <sub>J</sub> ≤ 150°C	50	V/ns	
T <sub>J</sub>		-55 ... +150	°C	
T <sub>JM</sub>		150	°C	
T <sub>stg</sub>		-55 ... +150	°C	
T <sub>L</sub>	Maximum Lead Temperature for Soldering	300	°C	
T <sub>SOLD</sub>	1.6 mm (0.062in.) from Case for 10s	260	°C	
F <sub>c</sub>	Mounting Force	30..120 / 6.7..27	N/lb	
Weight		10	g	

Symbol	Test Conditions (T <sub>J</sub> = 25°C Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV <sub>DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = 3mA	850		V
V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 8mA	3.5		V
I <sub>GSS</sub>	V <sub>GS</sub> = ± 30V, V <sub>DS</sub> = 0V		± 200	nA
I <sub>DSS</sub>	V <sub>DS</sub> = V <sub>DSS</sub> , V <sub>GS</sub> = 0V T <sub>J</sub> = 125°C		50	μA
			5	mA
R <sub>DS(on)</sub>	V <sub>GS</sub> = 10V, I <sub>D</sub> = 0.5 • I <sub>D25</sub> , Note 1		41	mΩ

**Features**

- Low Q<sub>G</sub>
- Avalanche Rated
- Low Package Inductance

**Advantages**

- High Power Density
- Easy to Mount
- Space Savings

**Applications**

- Switch-Mode and Resonant-Mode Power Supplies
- DC-DC Converters
- PFC Circuits
- AC and DC Motor Drives
- Robotics and Servo Controls

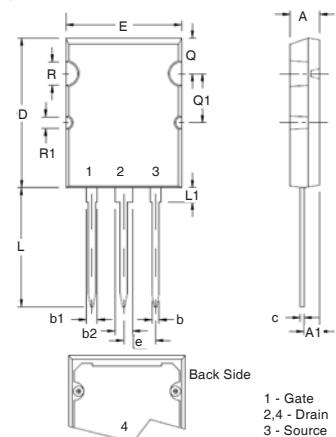
Symbol	Test Conditions (T <sub>J</sub> = 25°C, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max
<b>I<sub>fs</sub></b>	V <sub>DS</sub> = 10V, I <sub>D</sub> = 45A, Note 1	37	62	S
R <sub>Gi</sub>	Gate Input Resistance		0.60	Ω
C <sub>iss</sub>		13.3		nF
C <sub>oss</sub>		13.0		nF
C <sub>rss</sub>		220		pF
<b>Effective Output Capacitance</b>				
C <sub>o(er)</sub>	Energy related } V <sub>GS</sub> = 0V	395		pF
C <sub>o(tr)</sub>	Time related } V <sub>DS</sub> = 0.8 • V <sub>DSS</sub>	1820		pF
t <sub>d(on)</sub>		50		ns
t <sub>r</sub>		20		ns
t <sub>d(off)</sub>	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 0.5 • V <sub>DSS</sub> , I <sub>D</sub> = 45A	126		ns
t <sub>f</sub>	R <sub>G</sub> = 1Ω (External)	8		ns
Q <sub>g(on)</sub>		340		nC
Q <sub>gs</sub>	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 0.5 • V <sub>DSS</sub> , I <sub>D</sub> = 45A	78		nC
Q <sub>gd</sub>		190		nC
R <sub>thJC</sub>			0.07 °C/W	
R <sub>thCS</sub>		0.13		°C/W

### Source-Drain Diode

Symbol	Test Conditions (T <sub>J</sub> = 25°C, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
I <sub>s</sub>	V <sub>GS</sub> = 0V		90	A
I <sub>SM</sub>	Repetitive, Pulse Width Limited by T <sub>JM</sub>		360	A
V <sub>SD</sub>	I <sub>F</sub> = I <sub>S</sub> , V <sub>GS</sub> = 0V, Note 1		1.4	V
t <sub>rr</sub>		250		ns
Q <sub>RM</sub>	I <sub>F</sub> = 45A, -di/dt = 200A/μs	5.3		μC
I <sub>RM</sub>	V <sub>R</sub> = 100V, V <sub>GS</sub> = 0V	42.0		A

Note 1. Pulse test, t ≤ 300μs, duty cycle, d ≤ 2%.

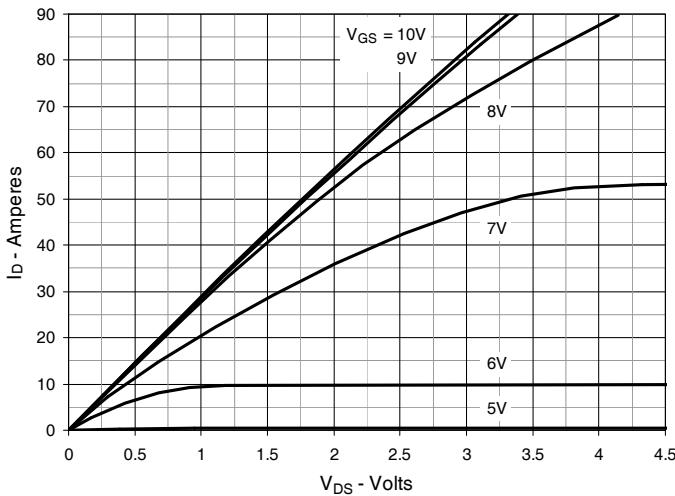
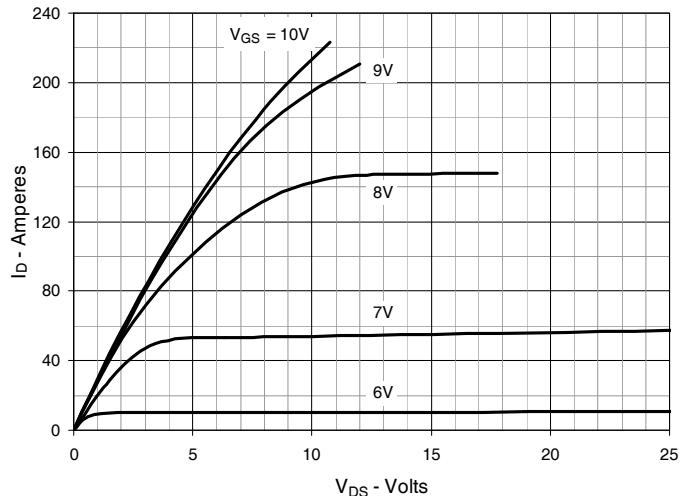
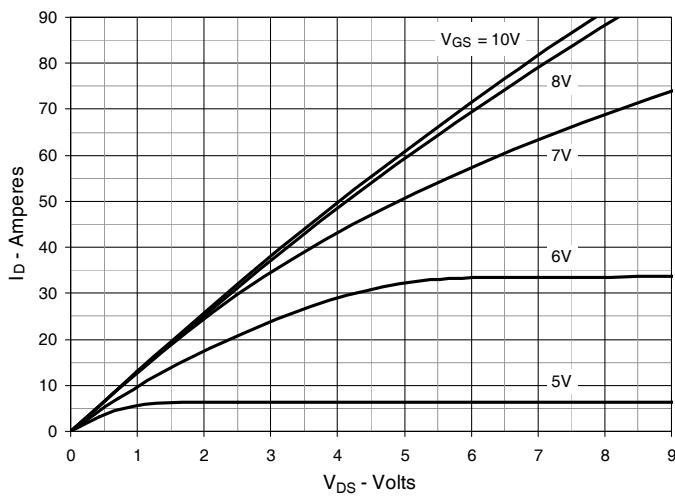
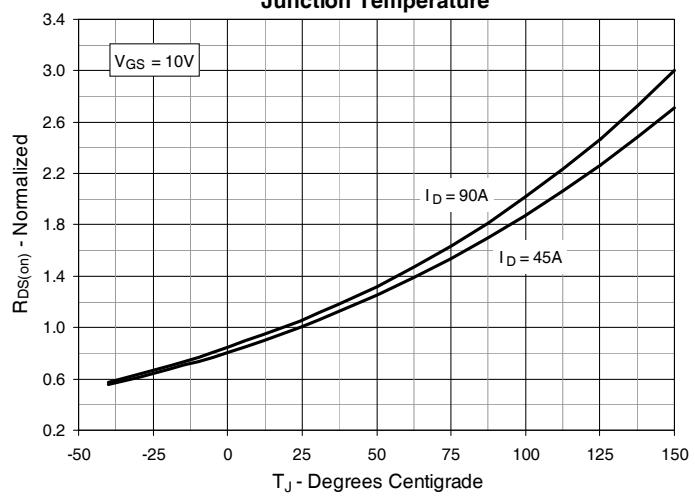
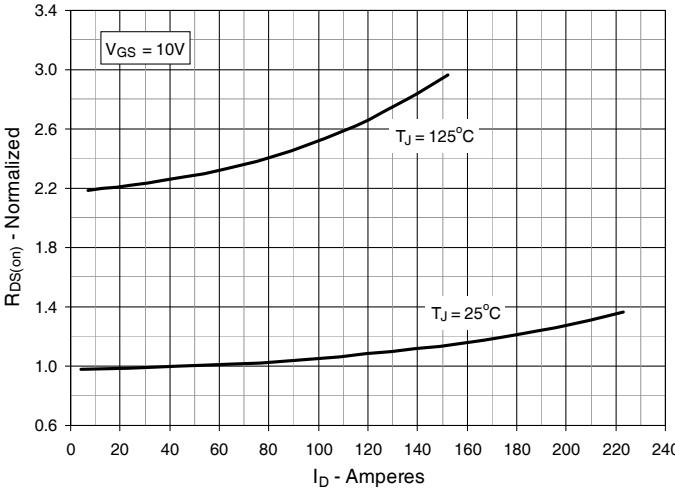
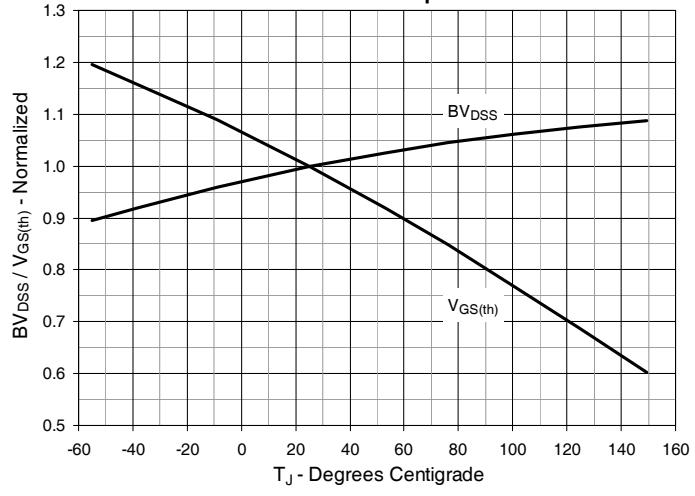
PLUS264™ (IXFB) Outline

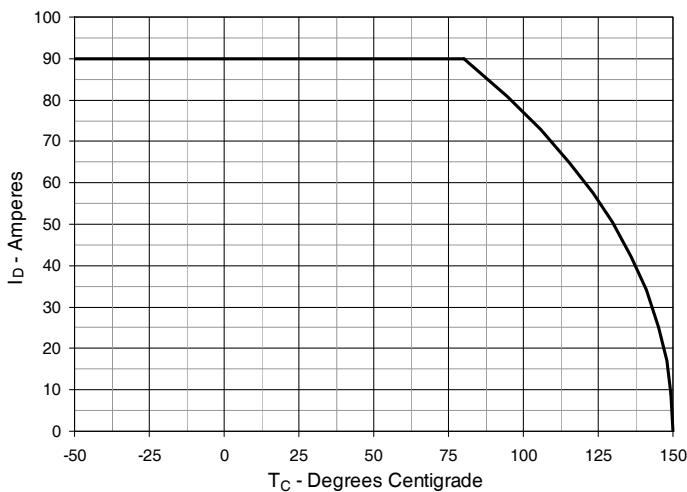
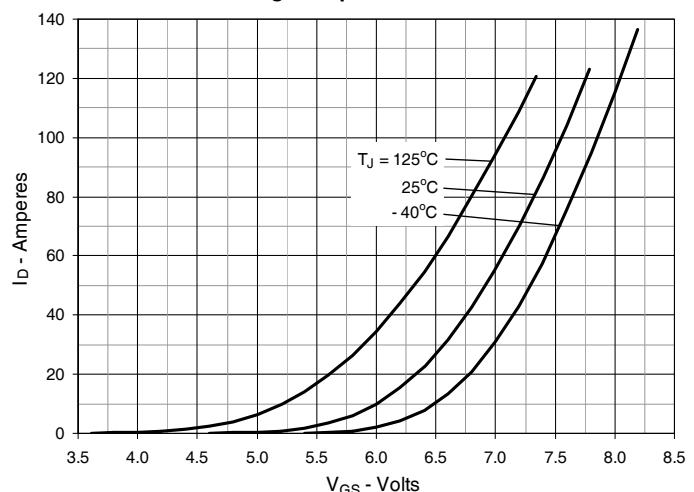
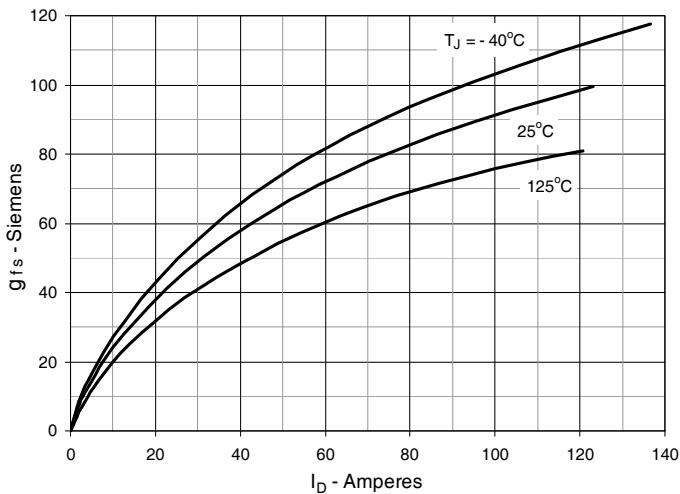
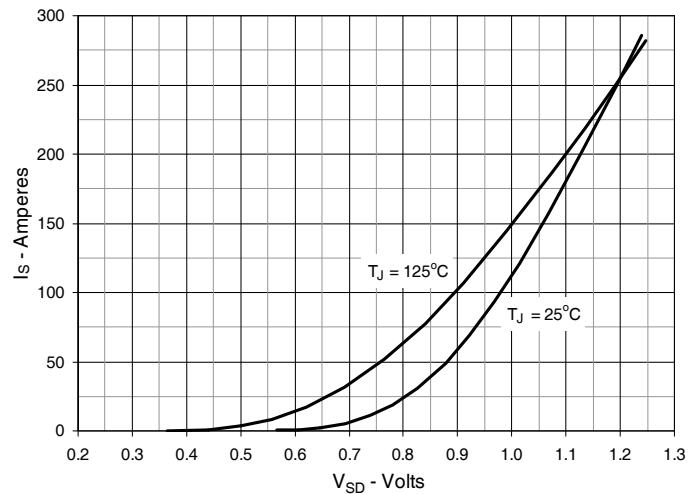
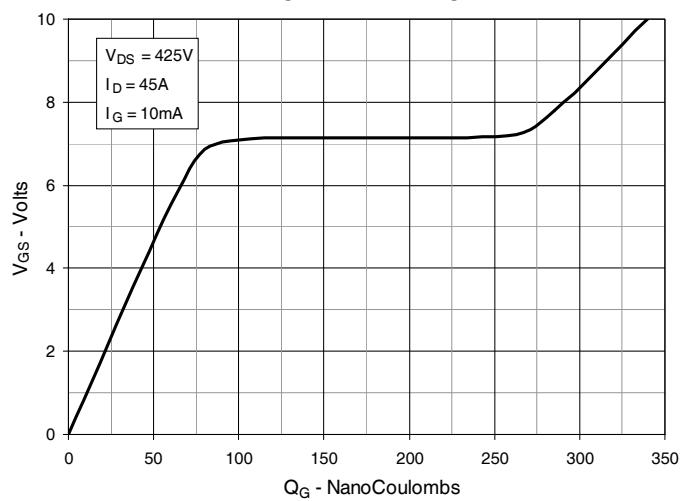
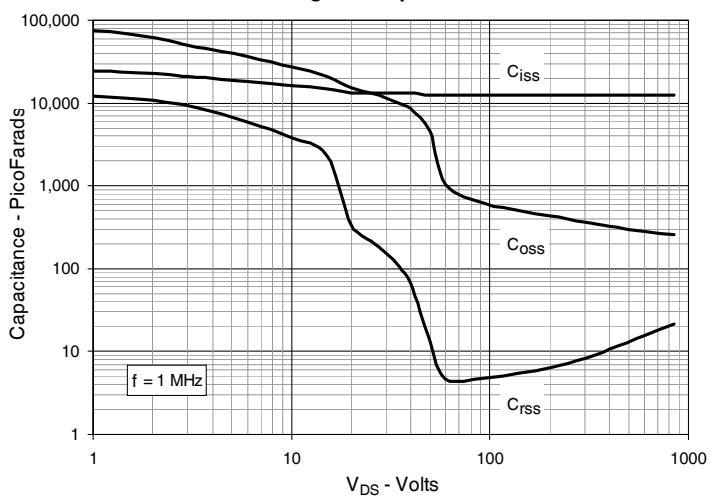


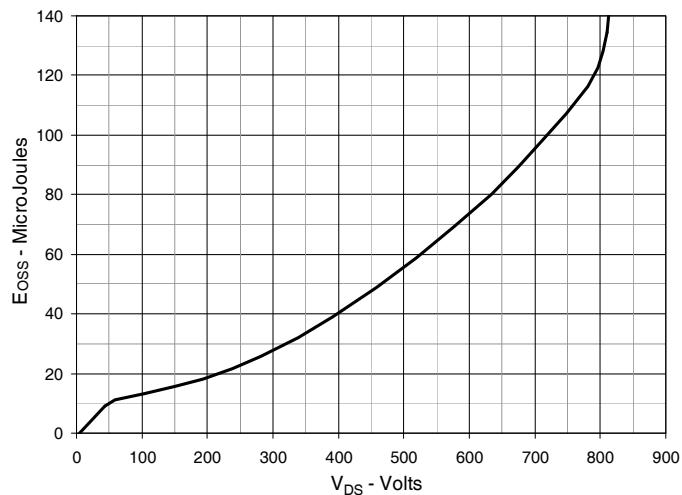
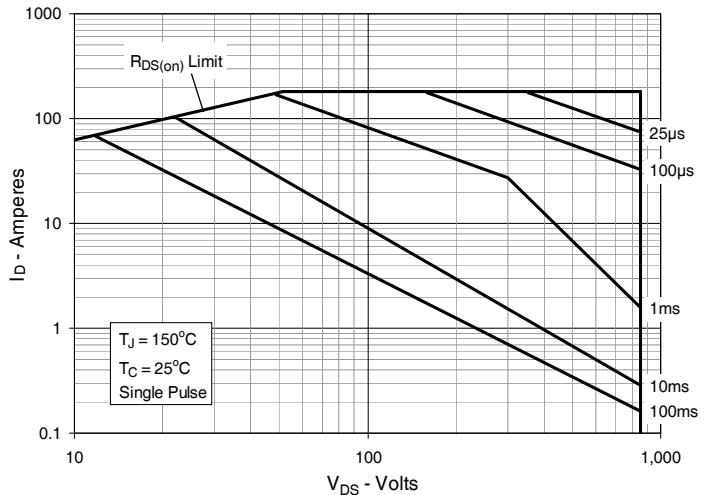
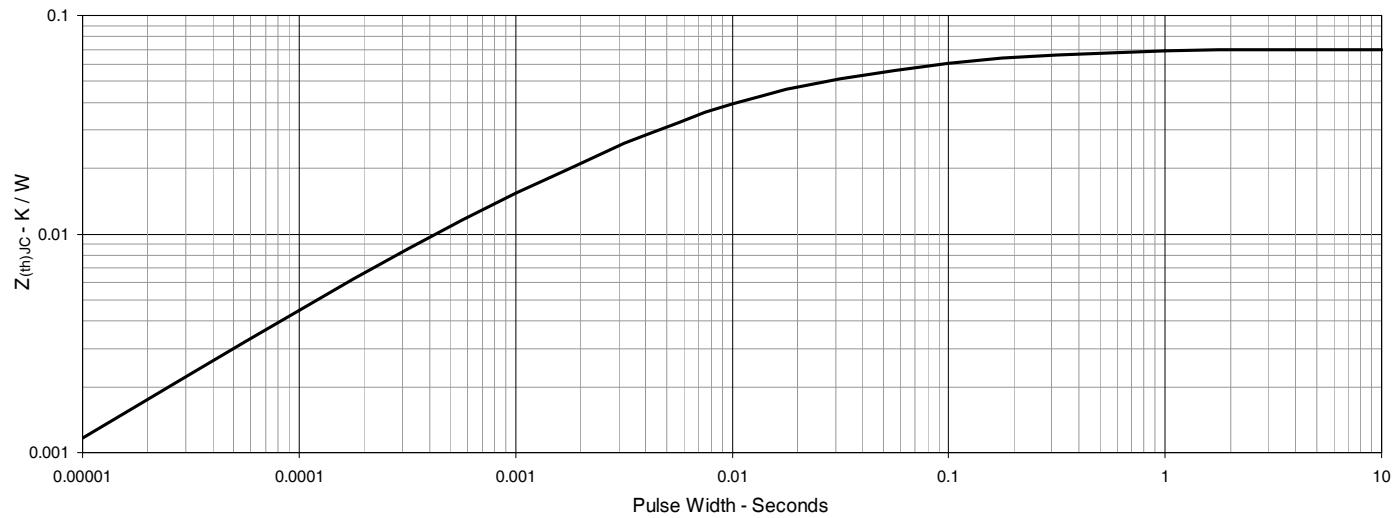
SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.185	.209	4.70	5.31
A1	.102	.118	2.59	3.00
b	.037	.055	0.94	1.40
b1	.087	.102	2.21	2.59
b2	.110	.126	2.79	3.20
c	.017	.029	0.43	0.74
D	1.007	1.047	25.58	26.59
E	.760	.799	19.30	20.29
e	.215 BSC		5.46 BSC	
L	.779	.842	19.79	21.39
L1	.087	.102	2.21	2.59
Q	.240	.256	6.10	6.50
Q1	.330	.346	8.38	8.79
ØR	.155	.187	3.94	4.75
ØR1	.085	.093	2.16	2.36

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**Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$** 

**Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$** 

**Fig. 3. Output Characteristics @  $T_J = 125^\circ\text{C}$** 

**Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = 45\text{A}$  Value vs. Junction Temperature**

**Fig. 5.  $R_{DS(on)}$  Normalized to  $I_D = 45\text{A}$  Value vs. Drain Current**

**Fig. 6. Normalized Breakdown & Threshold Voltages vs. Junction Temperature**


**Fig. 7. Maximum Drain Current vs. Case Temperature****Fig. 8. Input Admittance****Fig. 9. Transconductance****Fig. 10. Forward Voltage Drop of Intrinsic Diode****Fig. 11. Gate Charge****Fig. 12. Capacitance**

**Fig. 13. Output Capacitance Stored Energy****Fig. 14. Forward-Bias Safe Operating Area****Fig. 15. Maximum Transient Thermal Impedance**



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